

PATENT
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ABSTRACT OF THE DISCLOSURE

A method for depositing an organosilicate layer on a substrate includes varying one or more processing conditions during a process sequence for depositing an organosilicate layer from a gas mixture comprising an organosilicon compound in the presence of RF power in a processing chamber. In one aspect, the distance between the substrate and a gas distribution manifold in the processing chamber is varied during processing. Preferably, the method of depositing an organosilicate layer minimizes plasma-induced damage to the substrate.

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